Abstract

Method for producing a polished semiconductor wafer

The invention relates to a method for producing a polished semiconductor wafer, comprising the following steps in the stated order:
- slicing a semiconductor wafer from a rod composed of semiconductor material,
- material-removing processing of at least one side of the semiconductor wafer, and
- polishing of at least one side of the semiconductor wafer,
wherein the semiconductor wafer has after the material-removing processing and before the polishing on at least one side to be polished, along its edge, a ring-shaped local elevation having a maximum height of at least 0.1 µm, wherein the local elevation reaches its maximum height within a 10 mm wide ring lying at the edge of the semiconductor wafer.

Fig. 1